On page 6, line 18, after "formation" insert --of-- and insert commas after "is" and "course";

On page 6, line 26, after "depicting" delete "of";

On page 9, line 16, change the comma after "1-6" to a semicolon and insert a comma after "therefore";

On page 9, line 17, change "FIG." to --FIGS.--.

IN THE CLAIMS:

Please amend claims 23-25, and 27-28 as follows:

Subt F¹

23.   (Amended) A gate stack including a <u>non-crystalline</u> metallic silicide film [in a non-annealed state].

24.   (Amended) A gate stack, including a <u>crystalline</u> metallic silicide film [in an annealed state] wherein said metallic silicide <u>film</u> is substantially devoid of silicon clusters.

25.   (Amended) A gate stack on a dielectric layered semiconductor substrate, comprising:

a polysilicon layer disposed over said dielectric layered semiconductor substrate;

a <u>non-crystalline</u> metallic silicide film [in a non-annealed state] disposed over said polysilicon
layer; and

a dielectric cap on said <u>non-crystalline</u> metallic silicide film [formed at a sufficiently low
~~temperature that said metallic silicide film remains in said non-annealed state~~].

Subt F⁴

27.   (Amended) The gate stack structure of claim 26 wherein said a gate stack includes a [non-annealed] <u>non-crystalline</u> metallic silicide film.